

Atty Docket: ASMEX.376A

**FIG. 1**

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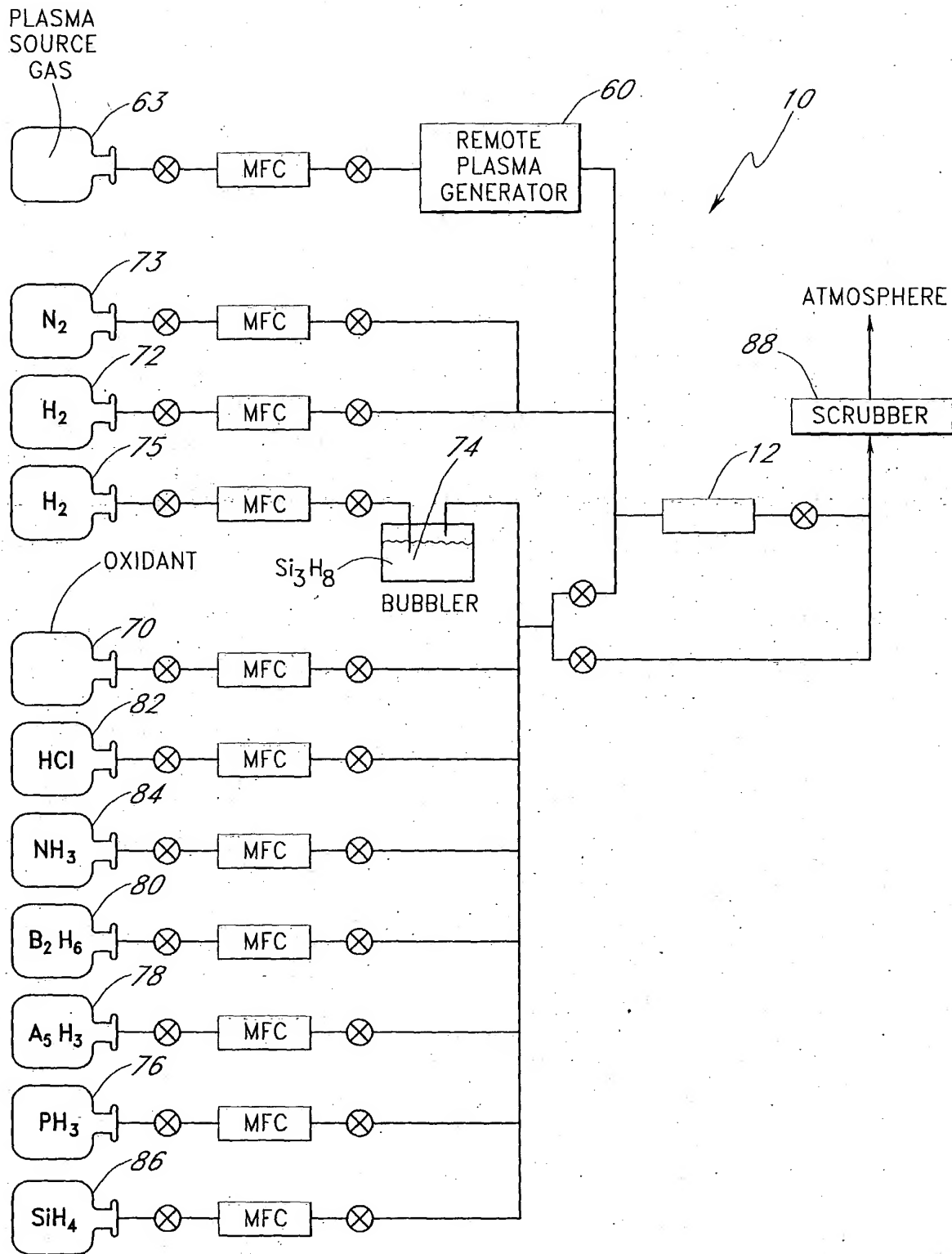
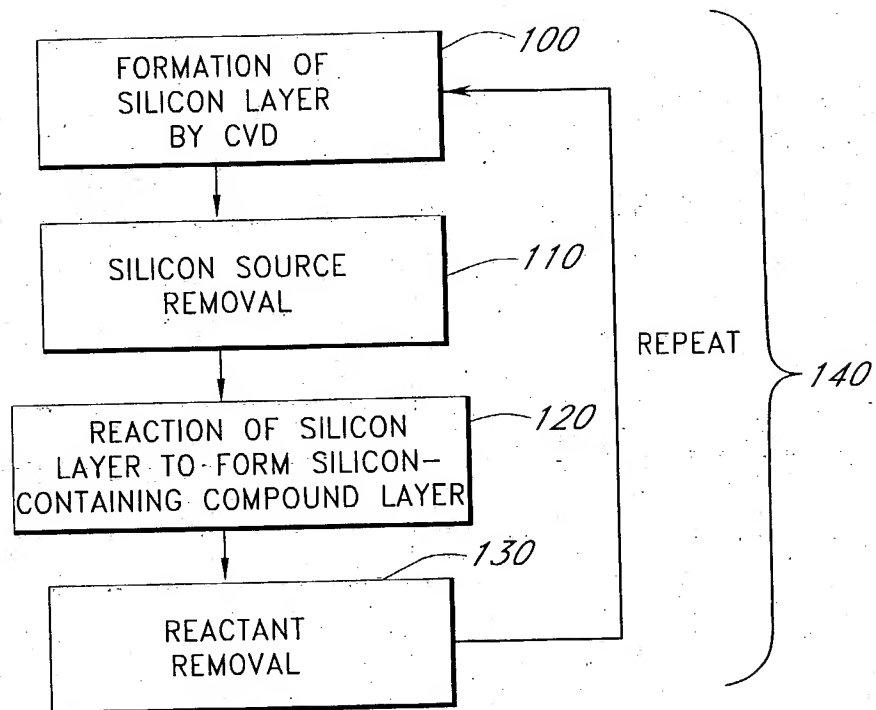


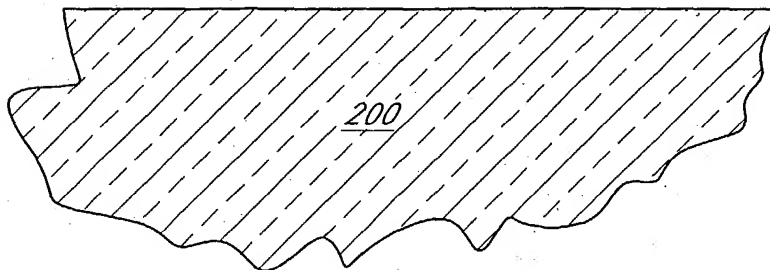
FIG. 2

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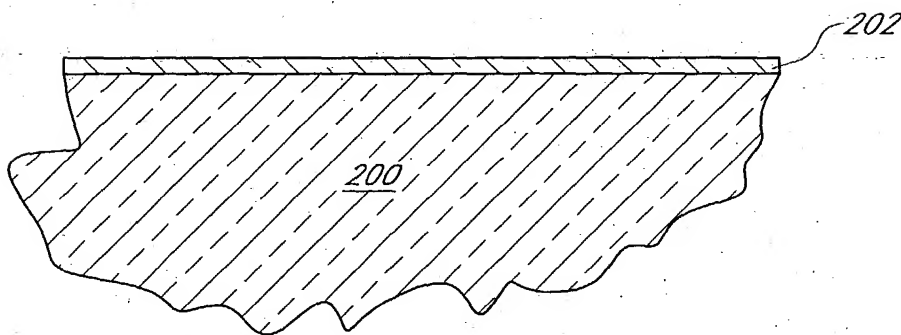


**FIG. 3**

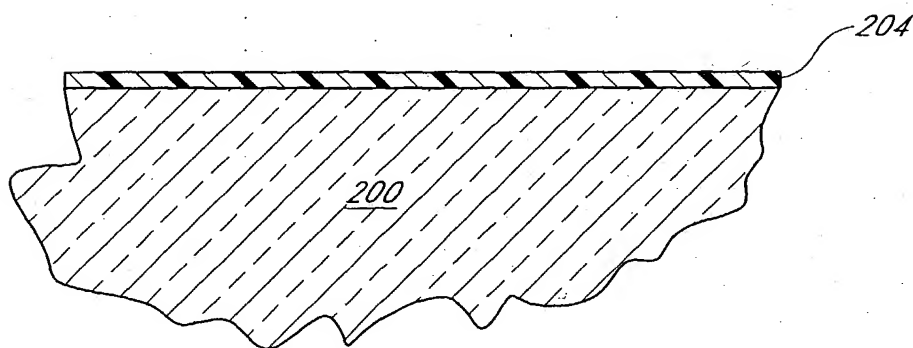
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**FIG. 4A**

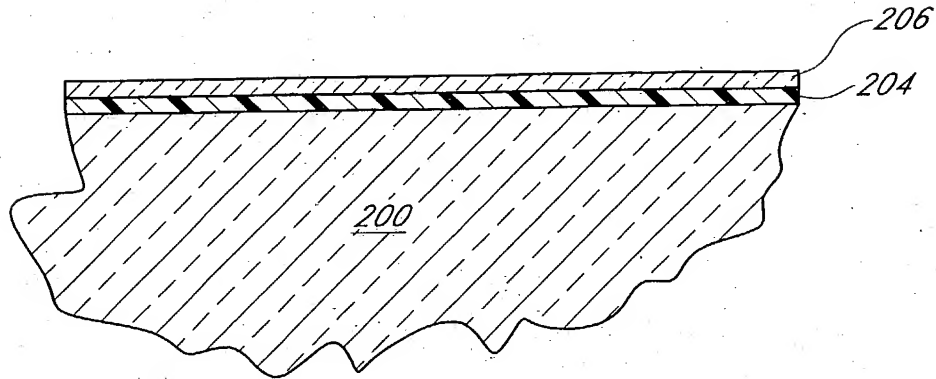


**FIG. 4B**

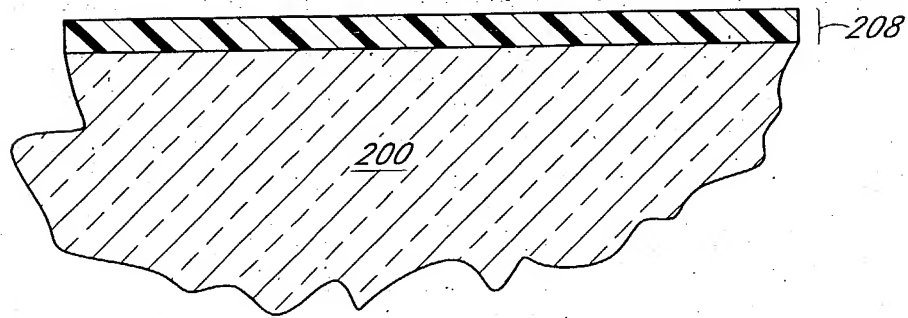


**FIG. 4C**

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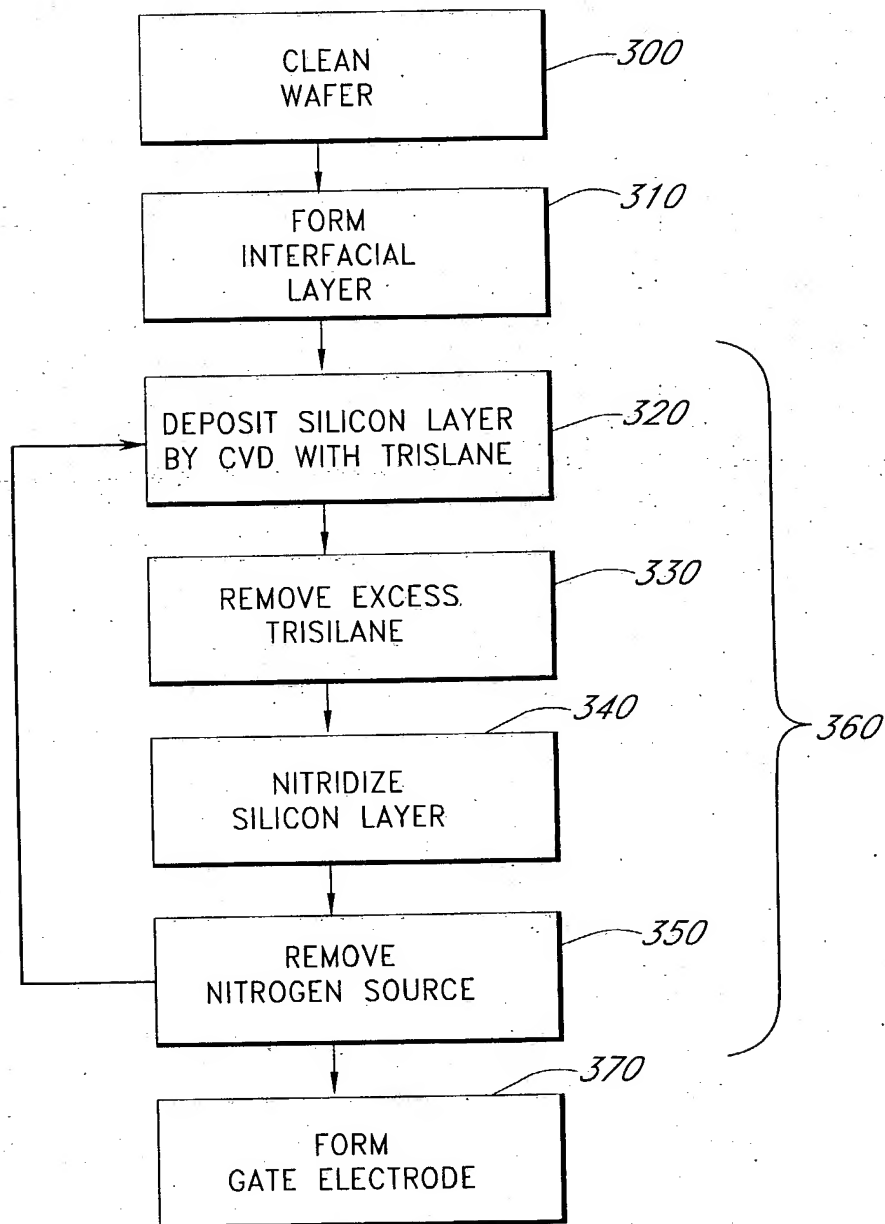


**FIG. 4D**



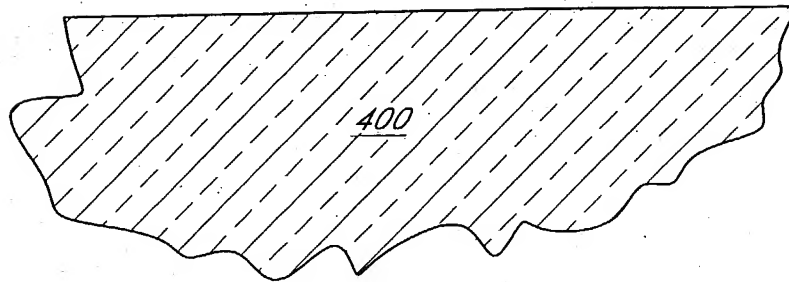
**FIG. 4E**

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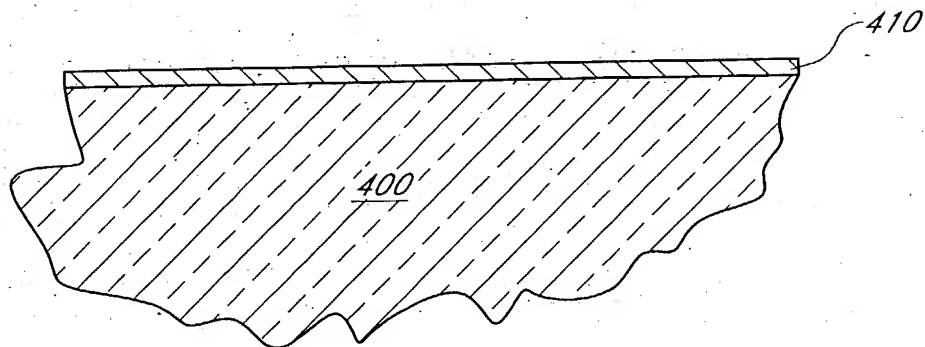


**FIG. 5**

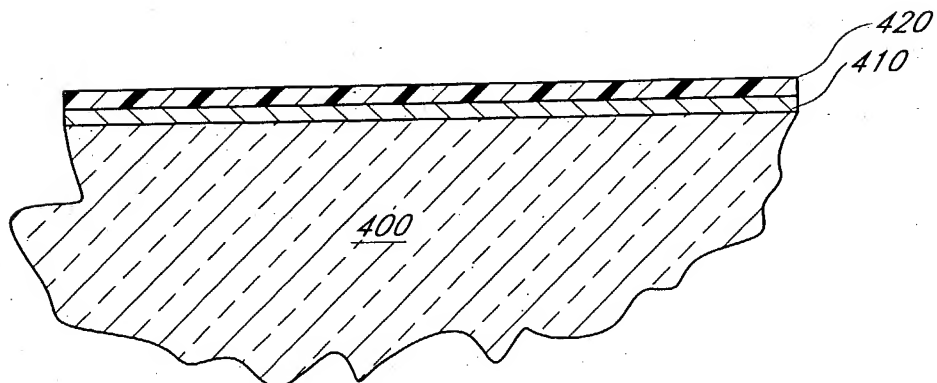
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**FIG. 6A**

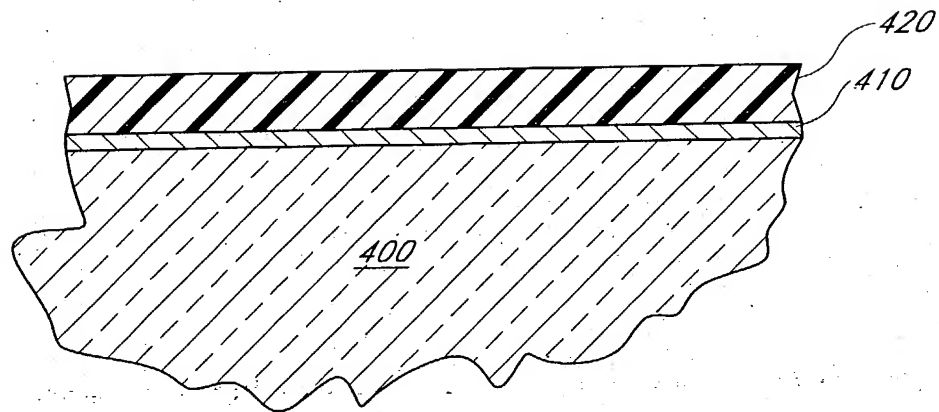


**FIG. 6B**

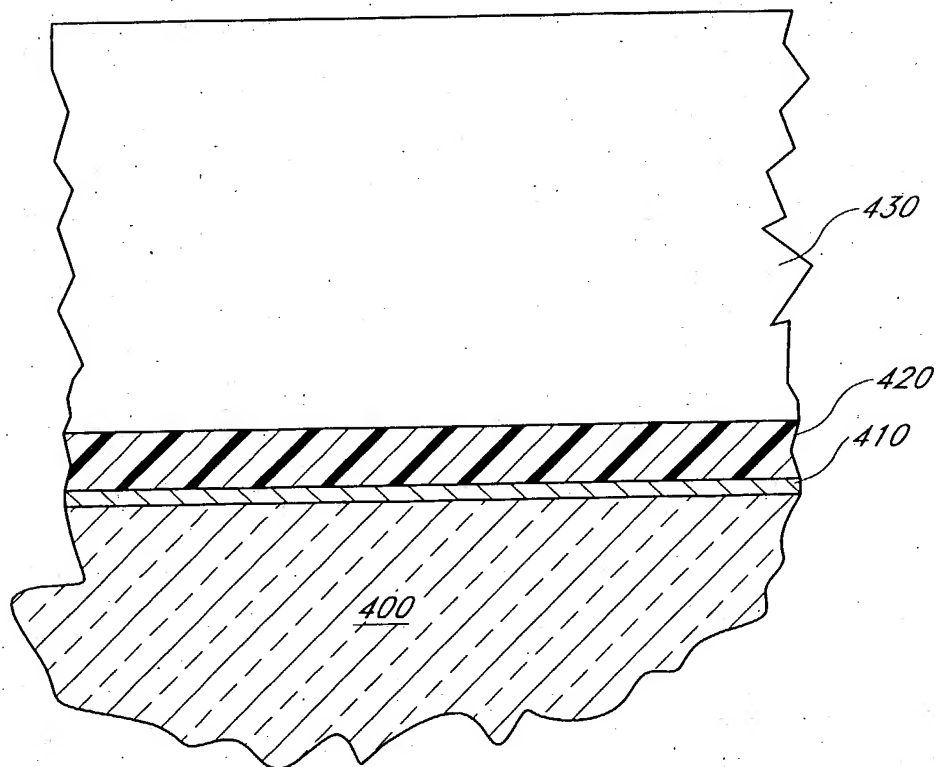


**FIG. 6C**

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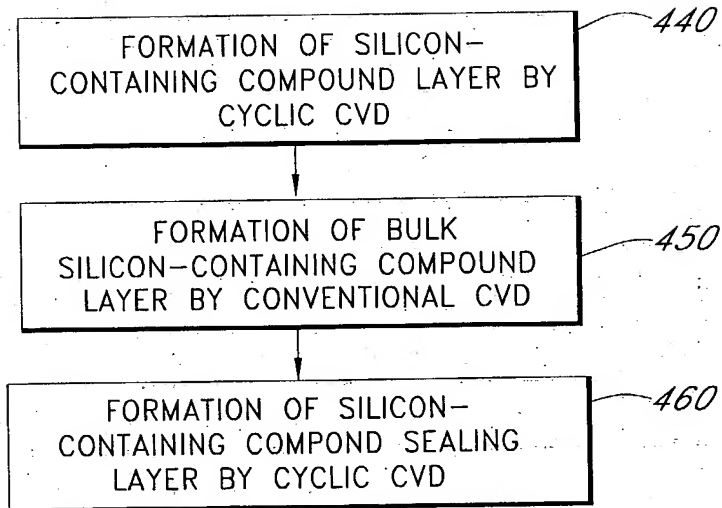
**FIG. 6D**



**FIG. 6E**



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**FIG. 7**

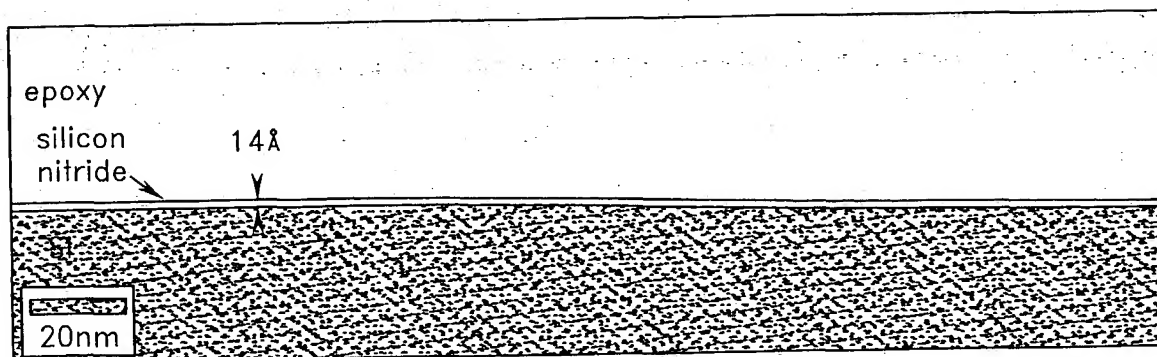
METHOD TO FORM ULTRA HIGH QUALITY SILICON-  
CONTAINING COMPOUND LAYERS

Todd et al.

Appl. No.: Unknown.

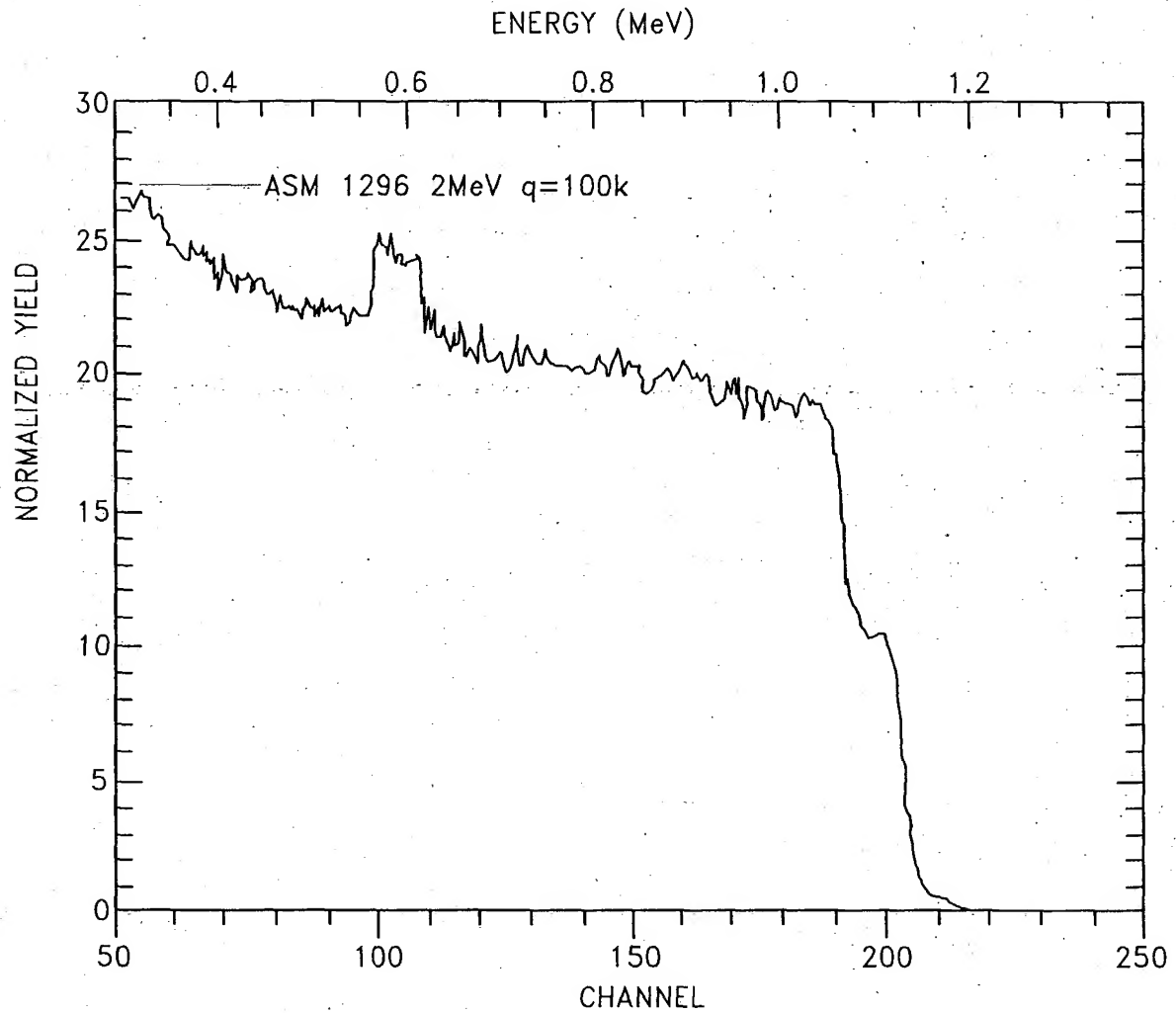
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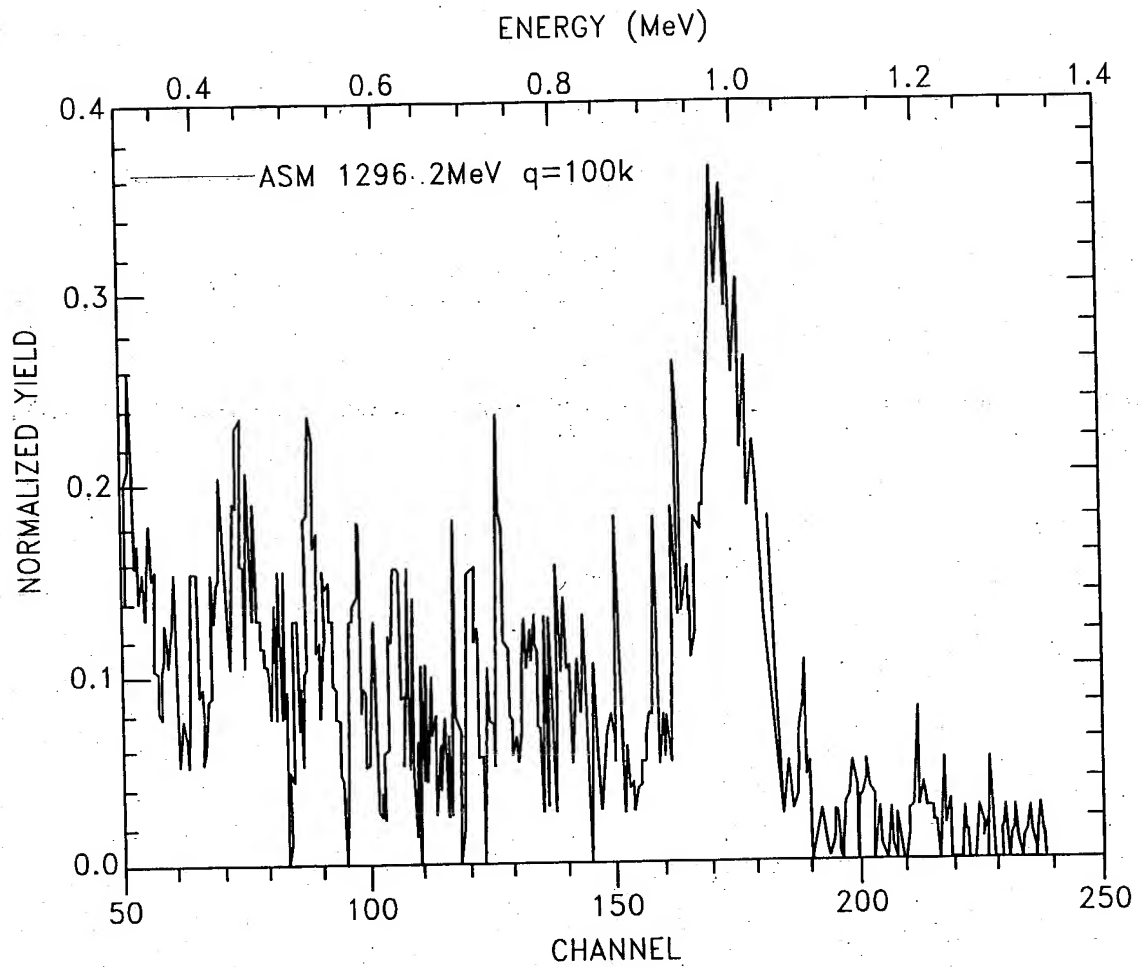
**FIG. 8**

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**FIG. 9**

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**FIG. 10**

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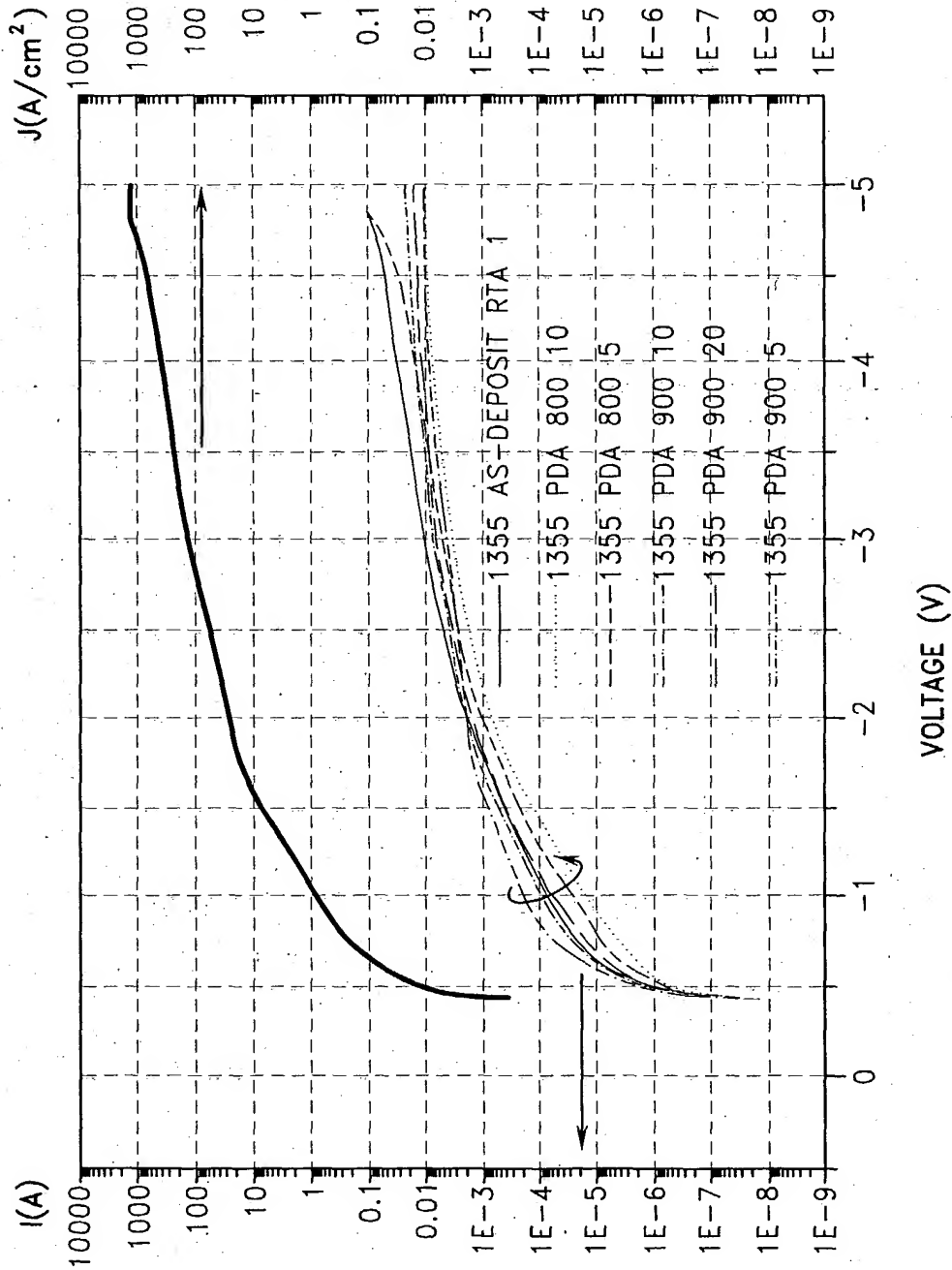


FIG. 11